



EpiGaN Expands GaN Epiwafer Production Using Aixtron G5+C MOCVD Technology

Hasselt, Belgium, Nov. 13, 2018 --- EpiGaN, a leading European supplier of Gallium Nitride (GaN) technology solutions for telecom, power electronics, and sensor applications, has chosen an Aixtron G5+C tool to meet growing demand from their global customer base.

EpiGaN, headquartered in Hasselt/Belgium, is a global supplier of GaN-on-Si and GaN-on-SiC material product solutions for next-generation semiconductor devices. The company has selected Aixtron's G5+C MOCVD system to boost its manufacturing capability of large-diameter GaN-on-Si and GaN-on-SiC epiwafers.

The new AIXTRON AIX G5+C reactor will be installed at EpiGaN's manufacturing site in Hasselt/Belgium and operational in Q1/2019. The fully automated Planetary[®] MOCVD system features in-situ chamber cleaning and enables configurations of 8x6 inch, or 5x8 inch epitaxial wafers to be automatically loaded and removed from the system in an enclosed cassette environment.

"The demand from our global customer base for GaN product solutions is booming. Our key customers are getting ready to launch and scale-up products based on our GaN RF-power technology, which is optimized for 5G broadband network applications. With Aixtron's AIX G5+C planetary system EpiGaN will increase its capacity for 150mm and 200mm product solutions to cope with these increasing market demands," says EpiGaN co-founder and CEO Dr Marianne Germain. "Aixtron's planetary system combines excellent on-wafer uniformity and run-to-run performance at the lowest cost of ownership – these attributes are critical to serve our customer base with products of exceptional performance and at the right price point."

Dr. Felix Grawert, President of AIXTRON, commented: "We are confident the AIX G5+C will support EpiGaN's demanding requirements for high-quality, cost-effective production of GaN epitaxial wafers as our tool meets the highest standards in terms of uniformity and particle density."

Just recently EpiGaN has released large-diameter versions of its HVRF (High Voltage Radio Frequency) GaN-on-Si, as well as GaN-on-SiC wafer product families tailored to demanding 5G applications needs. With the new Aixtron AIX G5+ MOCVD system EpiGaN expects to quickly scale up and spread out its differentiating technology solutions to the global market.

About EpiGaN

Founded in 2010 EpiGaN, provides innovative GaN technology solutions to its global customer base. From its European headquarters and modern production site in Hasselt/Belgium the company offers early access to leading-edge GaN/Si and GaN/SiC epiwafer technology for next-generation power switching, RF power, and advanced sensor solutions. EpiGaN's GaN technology is a key enabler for device innovation in consumer power supplies, electric vehicles, wireless charging and RF power systems for next-generation cellular infrastructures – 5G, IoT (Internet of Things), and smart sensor systems. The product spectrum ranges from application-specific standard epi-wafers of

up to 200mm diameter to customized products utilizing the company's differentiating technology of AlN barrier and in-situ SiN passivation layers.

For further information on EpiGaN nv, please visit our website at: www.epigan.com

About AIXTRON

AIXTRON SE is a leading provider of deposition equipment to the semiconductor industry. The company was founded in 1983 and is headquartered in Herzogenrath (near Aachen), Germany, with subsidiaries and sales offices in Asia, the United States and in Europe. AIXTRON's technology solutions are used by a diverse range of customers worldwide to build advanced components for electronic and opto-electronic applications based on compound or organic semiconductor materials. Such components are used in a broad range of innovative applications, technologies and industries. These include laser and LED applications, display technologies, data transmission, SiC and GaN power management and conversion, communication, signaling and lighting as well as a range of other leading-edge technologies.

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For further information on AIXTRON please visit our website at: www.aixtron.com.

EpiGaN Media Contact

Dr Markus Behet, CMO
EpiGaN nv
Kempische Steenweg 293
3500 Hasselt, Belgium
Tel.: +32 11 56 66 20
markus.behet@epigan.com

Aixtron Media Contact

Corporate Communications
Henning Marburger, Senior PR Manager
Aixtron SE
Dornkaulstr. 2
52134 Herzogenrath, Germany
Tel : +49 2407 9030-444
info@aixtron.com